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2N5432
N-CHANNEL SILICON JUNCTION FIELD-EFFECT TRANSISTORS

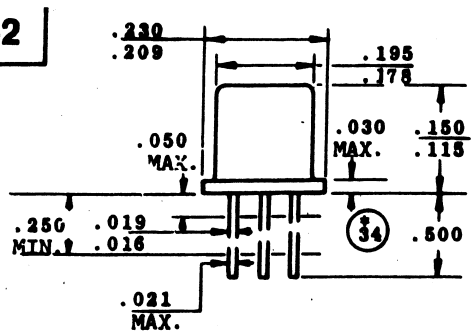
*ABSOLUTE MAXIMUM RATINGS (25°C)

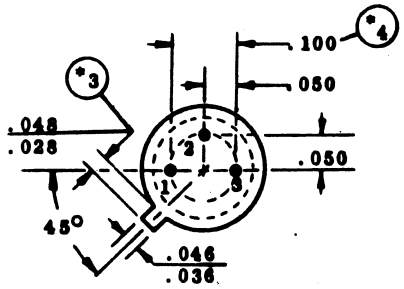
Reverse Gate-Drain or Gate-Source Voltage . . . . . -25 V
Gate Current . . . . . 100 mA
Drain Current . . . . . 400 mA
Total Device Dissipation at 25°C Free-Air Temperature . . . . . 300 mW
Storage Temperature . . . . . -65 to +150°C
Lead Temperature 1/16" from Case for 10 sec . . . . . 300°C

*ELECTRICAL CHARACTERISTICS (unless otherwise noted)

Characteristic		Test Conditions		2N5432 Min	2N5432 Max	Unit
BV_{GSS}	Gate Source Breakdown Voltage	$I_G = -1\ \mu A$, $V_{DS} = 0$		-25		V
I_{GSS}	Gate Reverse Current	$V_{GS} = -15$ V, $V_{DS} = 0$	25°C		-200	pA
			150°C		-200	nA
$I_{D(OFF)}$	Drain Cutoff Current	$V_{DS} = 5$ V, $V_{GS} = -10$ V	25°C		200	pA
			150°C		200	nA
V_P	Gate-Source Pinch-Off Voltage	$V_{DS} = 5$ V, $I_D = 3$ nA		-4	-10	V
I_{DSS}	Drain Current at Zero Gate Voltage (Note 3)	$V_{DS} = 15$ V, $V_{GS} = 0$		150		mA
r_{DS}	Static Drain-Source ON Resistance	$V_{GS} = 0$, $I_D = 10$ mA		2	5	ohm
$V_{DS(ON)}$	Drain-Source ON Voltage	$V_{GS} = 0$, $I_D = 10$ mA			50	mV
r_{ds}	Small-Signal Drain-Source ON Resistance	$V_{GS} = 0$, $I_D = 0$, $f = 1$ kHz			5	ohm
C_{iss}	Common-Source Input Capacitance	$V_{DS} = 0$, $V_{GS} = -10$ V, $f = 1$ MHz			30	pF
C_{rss}	Common Source Reverse Transfer Capacitance	$V_{DS} = 0$, $V_{GS} = -10$ V, $f = 1$ MHz			15	pF

TO-52





Quality Semi-Conductors